

L Number	Hits	Search Text	DB	Time stamp
3	1	kohashi.in.	JPO	2003/08/13 14:11
4	114	kohashi	JPO; DERWENT	2003/08/13 14:11
5	7	kohashi and semiconductor	JPO; DERWENT	2003/08/13 15:59
6	17887	die near3 bond\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/13 16:00
7	558	(die near3 bond\$3) and semiconductor near3 laser	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/13 16:01
8	151	(die near3 bond\$3) and semiconductor near3 laser near3 chip	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/13 16:57
9	404	braz\$3 near3 epoxy	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/13 16:58
10	123	braz\$3 near3 epoxy and fill\$3 and conduct\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/13 16:59
11	8	(braz\$3 near3 epoxy) and fill\$3 and conduct\$3 and (die near3 bond\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/13 17:06
12	23	(die near3 bond\$3) and (epoxy near3 resin) and (conduct\$3 near3 fill\$3) and (semiconductor near3 laser)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/13 17:15
13	3	(die near3 bond\$3) and (epoxy near3 resin) and (conduct\$3 near3 fill\$3) and (semiconductor near3 laser near3 chip)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/13 17:08
14	121	(die near3 bond\$3) and (epoxy near3 resin) and (conduct\$3 near3 fill\$3) and chip and laser	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/13 17:15
16	2	((die near3 bond\$3) and (epoxy near3 resin) and (conduct\$3 near3 fill\$3) and chip and laser) and 372/\$.cccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/13 17:16
15	32	((die near3 bond\$3) and (epoxy near3 resin) and (conduct\$3 near3 fill\$3) and chip and laser) and 438/\$.cccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/13 17:16
-	15	(die near bond\$3) and (laser near chip) and (epoxy near resin)	USPAT; US-PGPUB	2003/02/26 16:11